



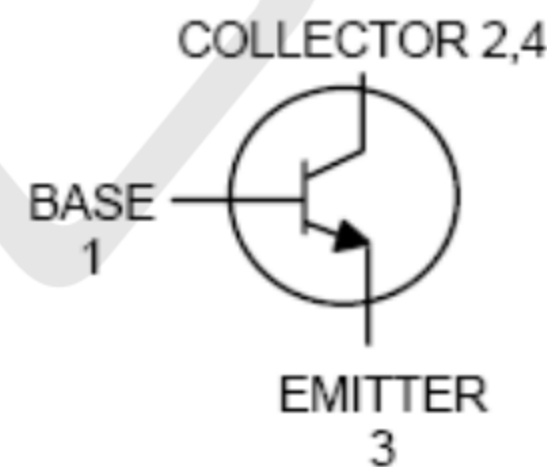
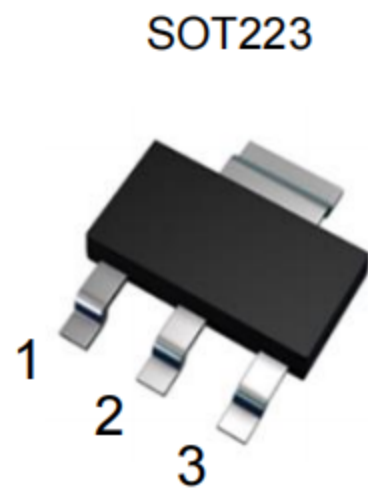
Features

- High Collector Current
- Low Collector-emitter Saturation Voltage

Mechanical Data

- Case: SOT-223
- Molding compound, UL flammability classification rating 94V-0
- Terminals: Matte tin plated leads, solderable per MIL-STD-202, Method 208

Circuit Diagram



Marking: ZT4401

Absolute Maximum Ratings (T_{amb}=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	-	60	V
V _{CEO}	collector-emitter voltage	open base	-	40	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current (DC)		-	600	mA
I _{CM}	peak collector current		-	800	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	1150	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C



Thermal Characteristic

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	109	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		28	K/W

Electrical Characteristics (TA=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	50	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 6\text{ V}$	–	50	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}$; see Fig.2 $I_C = 0.1\text{ mA}$ $I_C = 1\text{ mA}$ $I_C = 10\text{ mA}$ $I_C = 150\text{ mA}$; note 1	20 40 80 100	– – – 300	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}$; note 1	40	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$; note 1 $I_C = 500\text{ mA}; I_B = 50\text{ mA}$; note 1	– –	400 750	mV mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$; note 1 $I_C = 500\text{ mA}; I_B = 50\text{ mA}$; note 1	– –	950 1200	mV mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	–	8	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	30	pF
f_T	transition frequency	$I_C = 20\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	250	–	MHz
Switching times (between 10% and 90% levels); see Fig.3					
t_{on}	turn-on time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA};$ $I_{Boff} = -15\text{ mA}; V_{BB} = -3.5\text{ V};$ $V_{CC} = 29.5\text{ V}$	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns



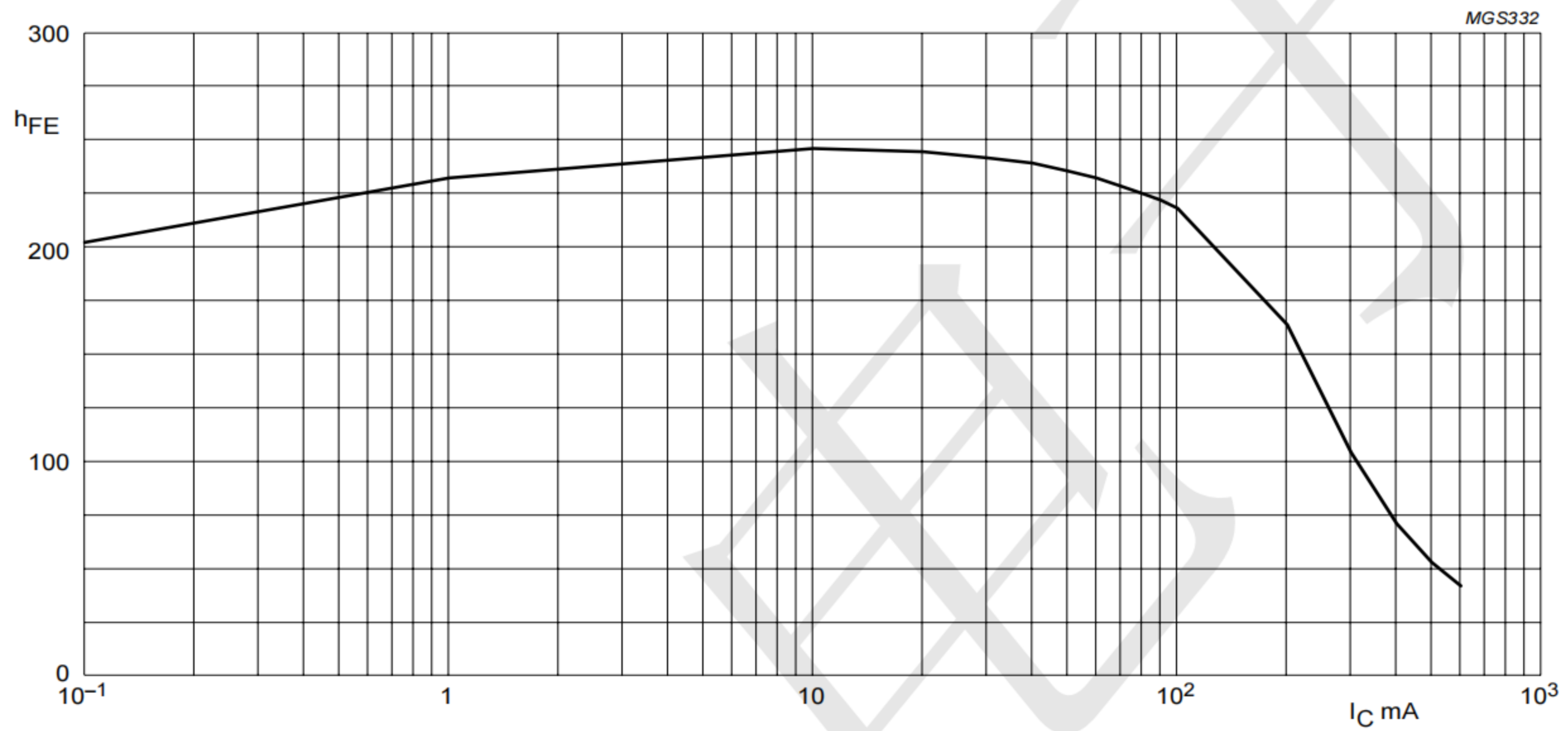
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TPPZT4401

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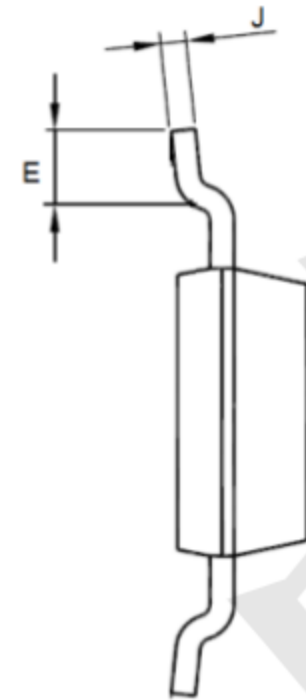
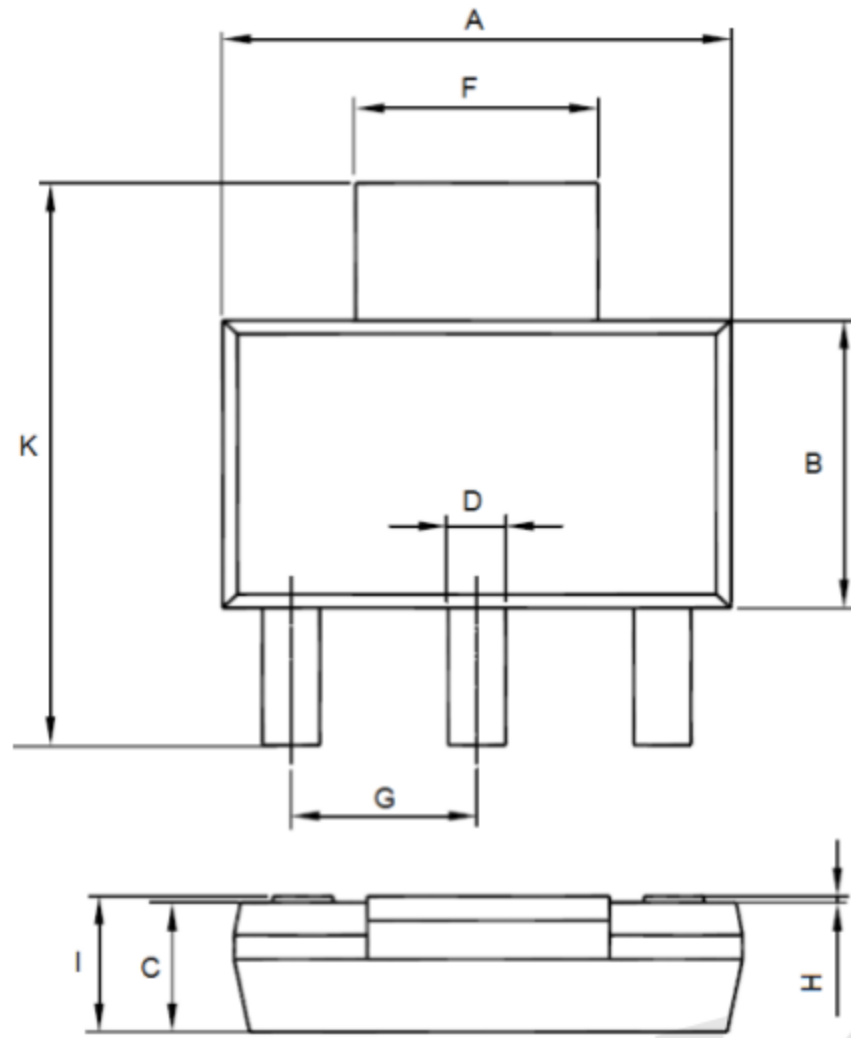
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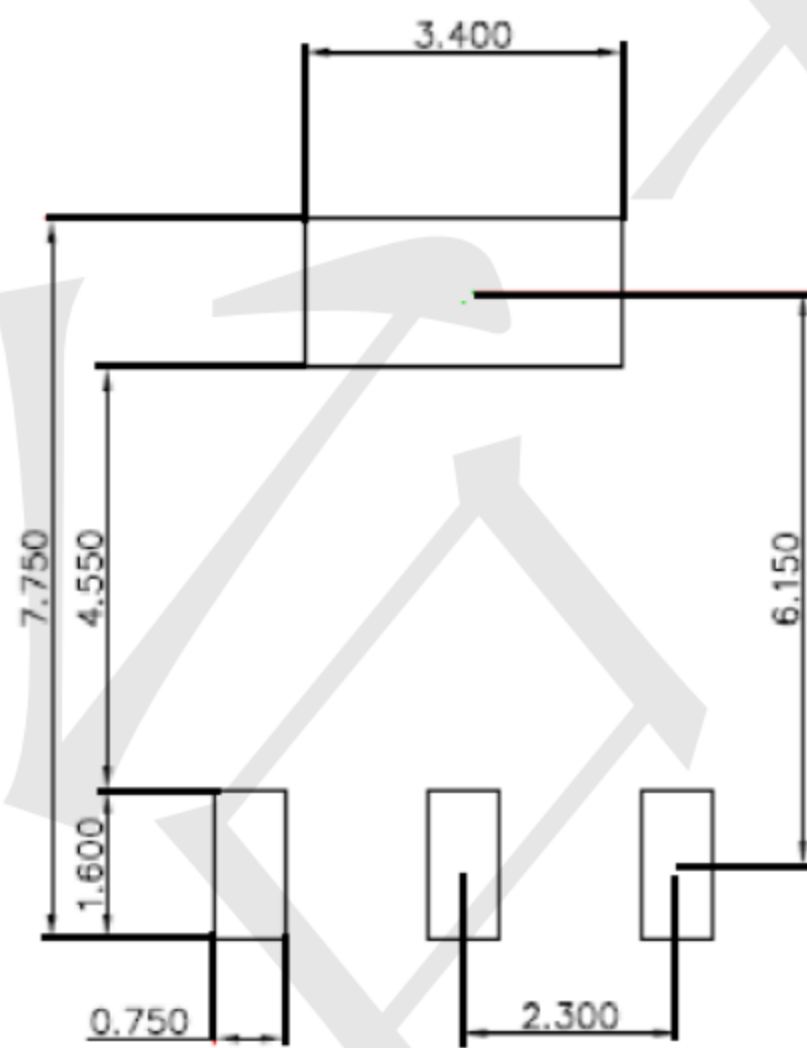
$V_{CE} = 1 V.$



Outline Drawing - SOT223



SOT-223		
Dim	Min	Max
A	6.10	6.50
B	3.30	3.70
C	1.50	1.70
D	0.66	0.82
E	0.90	1.15
F	2.90	3.10
G	2.20	2.40
H	0.02	0.10
I	1.52	1.80
J	0.20	0.40
K	6.70	7.30



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